NSN 5961-01-456-5058

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Inclosure Material:

Metal and ceramic

Overall Length:

Between 0.790 inches and 0.800 inches

Overall Height:

Between 0.249 inches and 0.260 inches

Overall Width:

Between 0.535 inches and 0.545 inches

Mounting Facility Quantity:

1

Internal Configuration:

Field effect

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-254aa

Mounting Method:

Unthreaded hole

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

200.0 breakdown voltage, drain-to-source, with all other terminals short-circuited to source and 20.0 gate to source voltage

Current Rating Per Characteristic:

18.00 amperes drain current and 18.00 amperes source current

Power Rating Per Characteristic:

125.0 watts total power dissipation

Maximum Operating Tempurature Per Measurement Point:

150.0 degrees celsius junction

Test Data Document:

81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Terminal Type And Quantity:

3 pin

Specification Data:

81349-mil-prf-19500/596 government specification

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0

Mil-std (military Standard):

Mil-prf-19500 spec.